IFW

File No.: 14836-8US-1 AD/mb

Montreal, Canada
March 9, 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Applicant:	MICROBRIDGE TECHNOLOGIES INC.
Serial No.:	10/796,421
Filed:	March 10, 2004
Title:	METHOD FOR TRIMMING RESISTORS
Group Art Unit:	3742
Examiner:	--
Agent of Record:	Alexandra Daoud Tel: (514) 847-4333

MAIL STOP – AMENDMENTS
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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT
PRIOR TO FIRST OFFICE ACTION

Sir:

Pursuant to the duty of disclosure under 37 CFR 1.56, copies of the references listed on the attached PTO Form SB08A/B are submitted herewith.

In accordance with 37 CFR 1.97(h), the submission of the present information is not to be construed as an admission that such information is, or is considered to be material to patentability.

The Examiner is kindly requested to consider these references during the examination of the above-identified application, making the references of record, and to return an initialed copy of the SB08A/B Form to the below-signed agent.

Respectfully submitted,

MICROBRIDGE TECHNOLOGIES INC.

By: _____

Alexandra Daoud, Registration No. 55,992
OGILVY RENAULT
Customer Number 020988

Enc.: Copies of references cited therein
2 sets of SB08A/B Form

PTO/SB/08A/B 08-03)
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 3

Complete if Known	
Application Number	**10/796, 421**
Filing Date	**March 10, 2004**
First Named Inventor	**Oleg GRUDIN et al.**
Art Unit	**3742**
Examiner Name	**(unknown)**
Attorney Docket Number	**14836-8US-1 AD/mb**

#U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number – Kind Code[2] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
		US-6,097,276	Aug. 1, 2000	Van Den Broek et al.	
		US-5,844,122	Dec. 1, 1998	Kato	
		US-5,635,893	Jun. 3, 1997	Spraggins et al.	
		US-5,493,148	Feb. 20, 1996	Ohata et al.	
		US-5,460,040	Oct. 24, 1995	Tada et al.	
		US-4,902,959	Feb. 20, 1990	Brokaw	
		US-5,757,264	May 26, 1998	Petit	
		US-4,717,886	Jan. 5, 1988	Davis et al.	
		US-4,683,442	Jul.28, 1987	Vyne	
		US-4,606,781	Aug. 19, 1986	Vyne	
		US-5,110,758	May 5, 1992	Baskett	
		US-5,563,549	Oct. 8, 1996	Shieh	
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document Country Code3 – Number4 – Kind Code5 *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant Of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T[6]
		WO 00/21196	Apr. 13, 2000	Honeywell Inc.		

Examiner Signature		Date Considered	

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This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. **SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria VA 22313-1450.**

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Art Unit	3742
Examiner Name	(unknown)
Attorney Docket Number	14836-8US-1 AD/mb

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T[2]
		Constant Voltage Trimming of Heavily Doped Polysilicon Resistors, Japan Journal Appl. Phys. Vol. 34, Part 1, No. 1, January 1995, pp. 48-53.	
		Pulse Current Trimming of Polysilicon Resistors, Transactions of Electron Devices, IEEE, Vol. 42, N° 4, April 1995, pp. 689-695.	
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		Electrical Trimming of Heavily Doped Polycrystalline Silicon Resistors, IEEE Transactions on Electron Devices, Vo. ED-26, No. 11, November 1979, pp. 738-742.	
		A Monolithic 14Bit D/A Converter Fabricated with a New Trimming Technique (DOT), IEEE, Journal of Solid-State Circuits, Vol. SC-19, N° 5, October 1984, pp. 802-807.	
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		Micromachined Thermal Radiation Emitter from a Commercial CMOS Process,IEEE Electron Devices Letters, Vol. 12, No. 2, February 1991, pp. 57-59.	

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T[2]
		CMOS-Compatible High-Temperature Micro-Heater: Microstructure Release and Testing, Can. J. Elect & Comp. Eng., Vol. 25, No. 1, January 2000, pp. 002-006.	
		Reliability Study of Polysilicon for Microhotplates, 1994, Dept. of Electrical and Computer Engineering, N.R. Swart et al., University of Waterloo, Waterloo, Ont. CANADA, pp. 119-122,	
		CMOS Thermally Isolated Heater Structure as a Substrate for Semiconductor Gas Sensors, S. Wessel et al, Energy Research Institute, pp. 1.6.1 to 1.6.8.	
		A Microstructure for Measurement of Thermal Conductivity of Polysilicon Thin Films, Friedemann Völklein et al., Jour. of Microelectromechanical Systems, Vol. 1, N° 4, Dec. 1992, pp. 193-196.	
		Electrical and Optical Characteristics of Vacuum-Sealed Polysilicon Microlamps, Carlos H. Mastrangelo et al., IEEE Transactions on Electron Devices, Vol. 39, N° 6, June 1992, pp. 1363-1374.	

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